

N-Channel 250-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$Rr_{DS(on)}\left(\Omega\right)$	I _D (A)		
250	0.155 at V _{GS} = 10 V	3.0		
	0.162 at V _{GS} = 6.0 V	2.9		

SO-8 S 1 8 D S 2 7 D S 3 6 D G 4 5 D

Top View

Ordering Information: Si4434DY-T1-E3 (Lead (Pb)-free)

Si4434DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

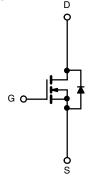
- Halogen-free According to IEC 61249-2-21 Definition
- PWM-Optimized TrenchFET® Power MOSFET
- 100 % R_q Tested
- Avalanche Tested



ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- · Primary Side Switch In:
 - Telecom Power Supplies
 - Distributed Power Architectures
 - Miniature Power Modules



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	250		V
Gate-Source Voltage		V _{GS}	± 20		V
Continuous Dunin Comment /T 150 9CV	T _A = 25 °C	1-	3.0	2.1	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	- I _D	2.4	1.7	ı
Pulsed Drain Current		I _{DM}	30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.6	1.3	
Avalanche Current	L = 0.1 mH	I _{AS}	13		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	8.4		mJ
Mariana Barra Biraira Biraira	T _A = 25 °C	P _D	3.1	1.56	W
Maximum Power Dissipation ^a	T _A = 70 °C	ı D	2.0	1.0	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana landia ta Andria 18	t ≤ 10 s	R _{thJA}	33	40	
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	65	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	17	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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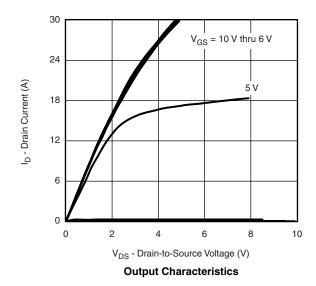
SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zoro Cata Valtaga Drain Current	l	V _{DS} = 250 V, V _{GS} = 0 V			1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			15		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
	В	$V_{GS} = 10 \text{ V}, I_D = 3.0 \text{ A}$		0.129	0.155		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 6.0 \text{ V}, I_D = 2.9 \text{ A}$		0.131	0.162	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 3.0 A		14		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.8 A, V _{GS} = 0 V		0.75	1.2	V	
Dynamic ^b	•		•		•		
Total Gate Charge	Q_g			34	50		
Gate-Source Charge	Q_{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.0 \text{ A}$		6.8		nC	
Gate-Drain Charge	Q_{gd}			10.5		1	
Gate Resistance	R_{g}		0.6	1.2	1.8	Ω	
Turn-On Delay Time	t _{d(on)}			16	25		
Rise Time	t _r	V_{DD} = 100 V, R_L = 25 Ω		23	35	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 4.0$ A, $V_{GEN}=10$ V, $R_g=6$ Ω		47	70		
Fall Time	t _f			19	30		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.8 A, dI/dt = 100 A/μs		100	150		

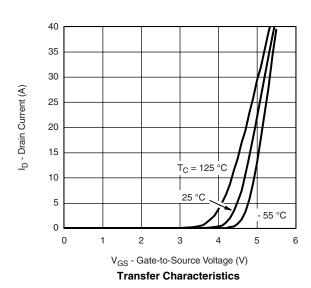
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



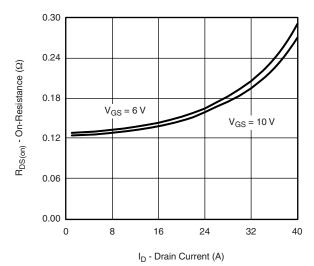




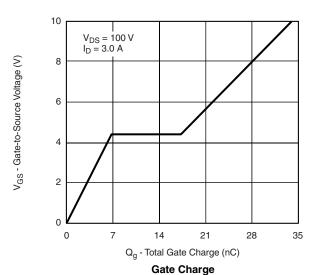


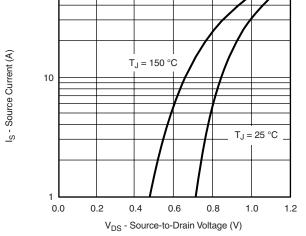


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

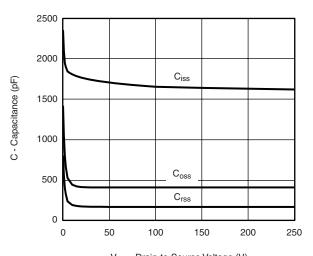


On-Resistance vs. Drain Current



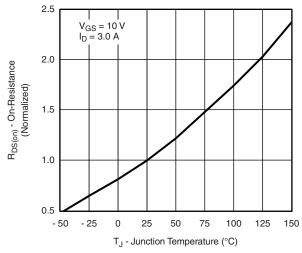


Source-Drain Diode Forward Voltage

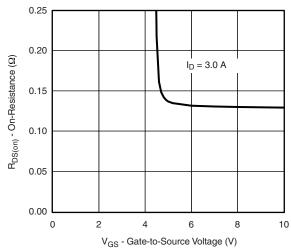


V_{DS} - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



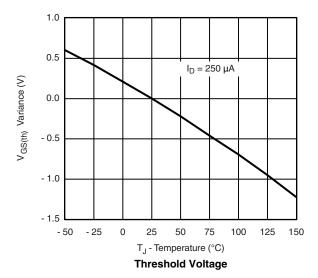
On-Resistance vs. Gate-to-Source Voltage

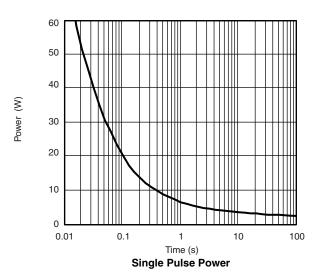
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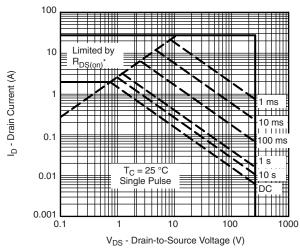
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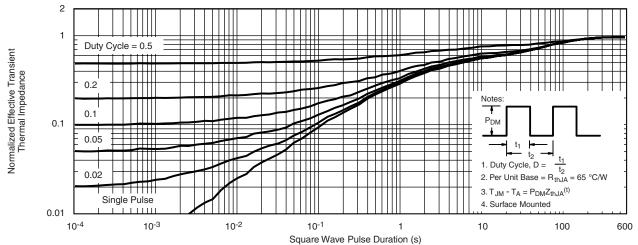
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





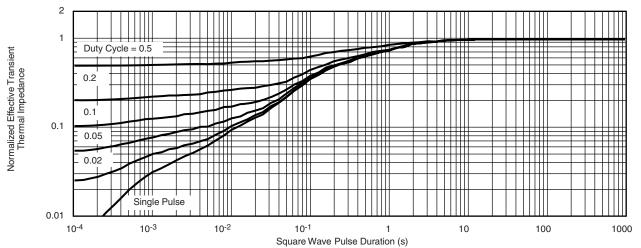


* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified **Safe Operating Area, Junction-to-Case**





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

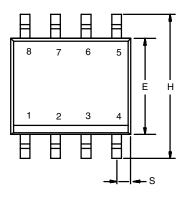


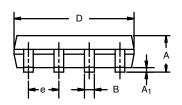
Normalized Thermal Transient Impedance, Junction-to-Foot

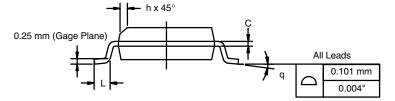
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

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APPLICATION NOTE



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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